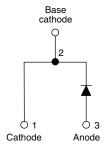


# HEXFRED® Ultrafast Soft Recovery Diode, 30 A



TO-247AC 2L



PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub>	30 A			
$V_{R}$	1200 V			
V <sub>F</sub> at I <sub>F</sub>	2.3 V			
t <sub>rr</sub> typ.	47 ns			
T <sub>J</sub> max.	150 °C			
Package	TO-247AC 2L			
Circuit configuration	Single			

#### **FEATURES**

- Ultrafast and ultrasoft recovery
- Very low I<sub>RBM</sub> and Q<sub>rr</sub>
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



ROHS COMPLIANT HALOGEN FREE

#### **BENEFITS**

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

#### **DESCRIPTION**

VS-HFA30PB120... is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 30 A continuous current, the VS-HFA30PB120... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (IRRM) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA30PB120... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Cathode to anode voltage	$V_R$		1200	V	
Maximum continuous forward current	I <sub>F</sub>	T <sub>C</sub> = 100 °C	30		
Single pulse forward current	I <sub>FSM</sub>	t <sub>p</sub> = 10 ms	120	Α	
Maximum repetitive forward current	I <sub>FRM</sub>		90		
Maximum power dissination	P <sub>D</sub>	T <sub>C</sub> = 25 °C	350	W	
Maximum power dissipation		T <sub>C</sub> = 100 °C	140	VV	
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C	



<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V <sub>BR</sub>	Ι <sub>R</sub> = 100 μΑ		1200	-	-	
		I <sub>F</sub> = 30 A		-	2.4	4.1	V
Maximum forward voltage V <sub>F</sub>	$V_{FM}$	I <sub>F</sub> = 60 A	See fig. 1	-	3.1	5.7	
		I <sub>F</sub> = 30 A, T <sub>J</sub> = 125 °C		-	2.3	4.0	
Maximum reverse		$V_R = V_R$ rated	Coo fig. 0	-	1.3	40	
leakage current	leakage current		See fig. 2		1100	4000	μΑ
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	See fig. 3	-	50	75	pF
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body - 8.0 - nh		nH			

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	47	-	
Reverse recovery time See fig. 5, 10	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 30 A	-	110	170	ns
occ lig. 5, 10	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	170	260	
Peak recovery current See fig. 6	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	10	15	А
	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C		-	16	24	
Reverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C	$dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	650	980	nC
See fig. 7	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	1540	2310	IIC
Peak rate of fall of recovery current during t <sub>b</sub> See fig. 8	dI <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	270	-	A/µs
	dI <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	240	_	-ν μδ

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	0.36	
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	40	°C/W
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth, and greased	-	0.50	-	
Weight			-	5.61	-	g
vveignt			-	0.198	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-247AC 2L	HFA30PB120			



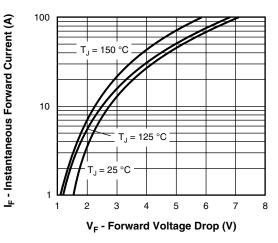


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

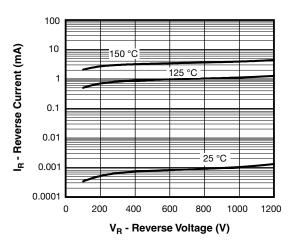


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

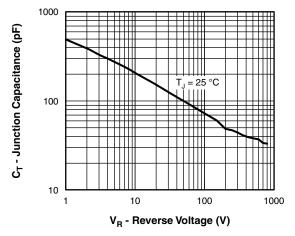


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

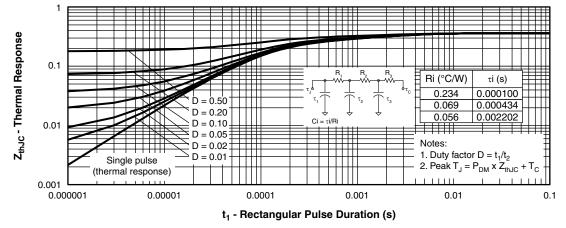


Fig. 4 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics

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## Vishay Semiconductors

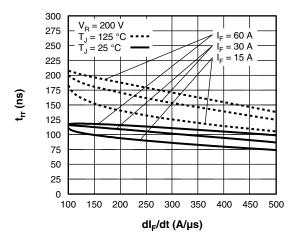


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>E</sub>/dt (Per Leg)

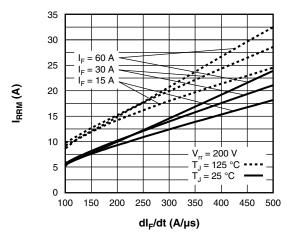


Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt (Per Leg)

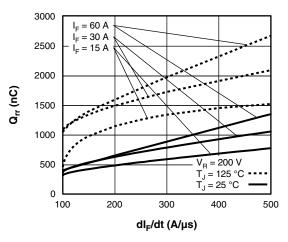


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt (Per Leg)

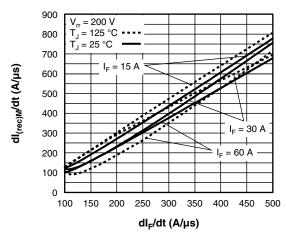
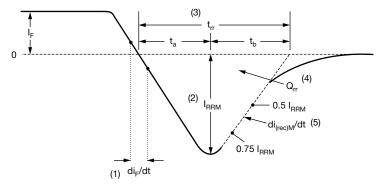


Fig. 8 - Typical dl<sub>(rec)M</sub>/dt vs. dl<sub>F</sub>/dt(Per Leg)



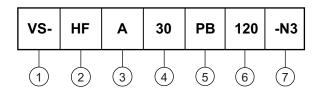
- di<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RBM</sub> and 0.50 I<sub>RBM</sub> extrapolated to zero current.
- (4)  $\mathbf{Q}_{\rm rr}$  area under curve defined by  $\mathbf{t}_{\rm rr}$  and  $\mathbf{I}_{\rm RRM}$ 
  - $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (5)  $di_{(rec)M}/dt$  peak rate of change of current during  $t_b$  portion of  $t_{rr}$

Fig. 9 - Reverse Recovery Waveform and Definitions



#### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - HEXFRED® family

Electron irradiated

4 - Current rating (30 = 30 A)

**5** - PB = TO-247AC, 2 pins

Voltage rating: (120 = 1200 V)

7 - Environmental digit:

-N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

ORDERING INFORMATION (Example)				
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION	
VS-HFA30PB120-N3	25	500	Antistatic plastic tube	

LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?96144</u>				
Part marking information <u>www.vishay.com/doc?95648</u>				



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